





LMR23630 JAJSEV6E - DECEMBER 2015 - REVISED AUGUST 2020

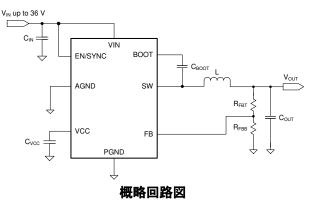
LMR23630 SIMPLE SWITCHER[®]、36V、3A、同期整流降圧コンバータ

1 特長

- 入力電圧範囲:4V~36V
- 3Aの連続出力電流
- 同期整流器内蔵
- 電流モード制御
- 最小スイッチ・オン時間:60ns
- 使いやすい内部補償
- 400kHz のスイッチング周波数と可変周波数を選択可
- PFM および強制 PWM モードのオプション
- 外部クロックへの周波数同期
- PFM オプションのとき、無負荷時の静止電流 75µA
- プリバイアス負荷へのソフト・スタート
- 高いデューティ・サイクルでの動作をサポート
- 高精度イネーブル入力
- ヒカップ・モードによる出力短絡保護
- 過熱保護機能
- PowerPAD[™] 付き 8 ピン HSOIC パッケージ
- PowerPAD[™] 付き 12 ピン WSON ウェッタブル・フラ ンク・パッケージ
- LMZM33603 モジュールを使用して、開発期間を短縮
- WEBENCH[®] Power Designer により、LMR23625 を 使用するカスタム設計を作成

2 アプリケーション

- ファクトリおよびビルディング・オートメーション・システ ム: PLC CPU、 HVAC 制御、 エレベータ制御
- アセット・トラッキング
- 汎用の広 VIN レギュレーション



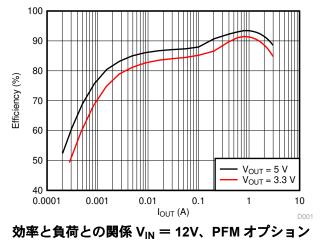
3 概要

LMR23630 SIMPLE SWITCHER[®] は、使いやすい 36V、3A 同期整流降圧レギュレータです。4V~36V とい う広い入力電圧範囲により、非レギュレーション電源からの 電源調整を行うさまざまな産業用アプリケーションに適して います。ピーク電流モード制御の採用によって、単純な制 御ループ補償とサイクル単位の電流制限を実現していま す。静止電流が 75µA であるため、バッテリ駆動のシステ ムに適しています。シャットダウン電流も 2µA と極めて低 いことから、バッテリ駆動時間のさらなる延長が可能です。 内部ループ補償により、ユーザーはループ補償を設計す る煩雑な作業から解放されます。これによって、外付け部 品の数も最小限に抑えられます。LMR23630 では、軽負 荷時に出力電圧リップルを小さくするための、固定周波数 FPWM モードを選択できます。 拡張ファミリ (HSOIC) とし て、1A (LMR23610) および 2.5A (LMR23625) の負荷 電流オプションを提供しており、いずれもピン互換パッケ ージを採用しているため、PCBレイアウトの簡素化と最適 化が可能になります。高精度のイネーブル入力により、レ ギュレータの制御とシステムの電源シーケンスが単純化さ れます。保護機能として、サイクル単位の電流制限、ヒカッ プ・モードの短絡保護、過剰な消費電力によるサーマル・ シャットダウンが搭載されています。

製品情報

部品番号 ⁽¹⁾	パッケージ	本体サイズ (公称)	
LMR23630	HSOIC (8)	4.89mm × 3.90mm	
	WSON (12)	3.00mm × 3.00mm	

利用可能なすべてのオプションに対応する詳細部品番号につい (1)ては、巻末の注文情報を参照してください。



英語版のTI製品についての情報を翻訳したこの資料は、製品の概要を確認する目的で便宜的に提供しているものです。該当する正式な英語版の最新情報は、 🐼 www.ti.com で閲覧でき、その内容が常に優先されます。 TI では翻訳の正確性および妥当性につきましては一切保証いたしません。 実際の設計などの前には、必ず 最新版の英語版をご参照くださいますようお願いいたします。



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Cł	nanges from Revision D (February 2018) to Revision E (July 2020)	Page
•	文書全体にわたって表、図、相互参照の採番方法を更新	1
•	<i>セクション</i> 1 に、LMZM33630 の項目を追加	1

Changes from Revision C (June 2017) to Revision D (February 2018)

Changes from Revision C (June 2017) to Revision D (Febru	Jary 2018)	Page
 「アプリケーション」のプログラマブル・ロジック・コントローラの電源 		ーートメーション・シ
ステムに変更		
・「アプリケーション」の多機能プリンタと産業用電源を削除		1
・「アプリケーション」の HVAC システムを汎用の広 VIN レギュレー		
 Added "2.2-µF, 16-V" for VCC pin bypass capacitor 		
Change the Max Recommend Operating Condition for lout t		
Consolidating all the common EC table characteristic betwe		
Input Voltage, VIN_UVLO, I _{EN} and Mnimum turn-on time		
Changed Typical Value for VIN_UVLO Rising threshold typic	cal from 3.6-V to 3.7-V and minir	mum Falling
threshold from 3-V to 2.9-V		7
• Changed the operating from "4.5-V" to "4-V" in Device Fu	Inctional Modes	20
• Changed from V _{OUT} = 7 V to 36 V to V _{IN} = 7 V to 36 V on \boxtimes] 9-9	
Changes from Revision B (April 2017) to Revision C (June	2017)	Page
 「アプリケーション」の車載用バッテリ・レギュレーションを削除 		1
• WSON パッケージおよびオプションを追加		1
Added Device Comparison Table		
Change EN Abs Max to EN/SYNC Abs Max		
Updating ESD Ratings to include HSOIC and WSON		
Corrected Equation 17 denominator from "(Vour x Voo)" to '	"(Vour + Voo)"	23

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С	hanges from Revision A (July 2016) to Revision B (April 2017)	Page
•	Changed spec from 6.0 to 6.2 for max under Current Limit	7
•	Changed spec from 4.2 to 4.6 for max under Current Limit	7
_		

Changes from Revision * (December 2015) to Revision A (July 2016)	Page

•	開発中から量産データに変更、残るすべてのセクションを追加。1

3



5 Device Comparison Table

PACKAGE	PART NUMBER	FIXED 400 kHz	ADJUSTABLE FREQUENCY RESISTOR	POWER GOOD	FPWM
HSOIC (8)	LMR23630ADDA	yes	no	no	no
	LMR23630AFDDA	yes	no	no	yes
	LMR23630DRR	no	yes	no	no
WSON (12) (Pin 6 is RT)	LMR23630FDRR	no	yes	no	yes
WSON (12) (Pin 6 is PGOOD)	LMR23630APDRR	yes	no	yes	no

6 Pin Configuration and Functions

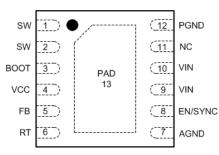


図 6-1. DRR Package 12-Pin WSON With RT and Thermal Pad Top View

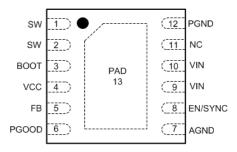


図 6-2. DRR Package 12-Pin WSON With PGOOD and Thermal Pad Top View

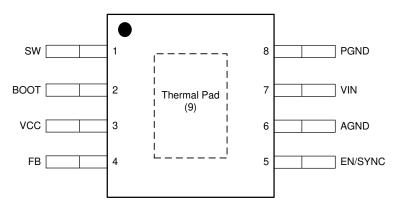


図 6-3. DDA Package 8-Pin HSOIC Top View



Pin Functions

PIN				I/O (1)	DESCRIPTION	
HSOI C	WSON With RT	WSON With PGOOD	NAME			
1	1, 2	1, 2	SW	Р	Switching output of the regulator. Internally connected to both power MOSFETs. Connect to power inductor.	
2	3	3	BOOT	Р	Boot-strap capacitor connection for high-side driver. Connect a high quality 100nF or 470nF capacitor from BOOT to SW.	
3	4	4	VCC	Р	Internal bias supply output for bypassing. Connect 2.2- μ F, 16-V bypass capacitor from this pin to AGND. Do not connect external loading to this pin. Never short this pin to ground during operation.	
4	5	5	FB	A	Feedback input to regulator, connect the midpoint of feedback resistor divider to this pin.	
N/A	6	N/A	RT	A	Connect a resistor RT from this pin to AGND to program switching frequency. Leave floating for 400-kHz default switching frequency.	
N/A	N/A	6	PGOOD	A	Open drain output for power-good flag. Use a $10-k\Omega$ to $100-k\Omega$ pullup resistor to logic rail or other DC voltage no higher than 12 V.	
5	8	8	EN/SYNC	A	Enable input to regulator. High = On, Low = Off. Can be connected to VIN. Do not float. Adjust the input undervoltage lockout with two resistors. The internal oscillator can be synchronized to an external clock by coupling a positive pulse into this pin through a small coupling capacitor. See $\frac{1}{2}/\sqrt{2}$ $\frac{3.4}{2}$ for details.	
6	7	7	AGND	G	Analog ground pin. Ground reference for internal references and logic. Connect to system ground.	
7	9, 10	9, 10	VIN	Р	Input supply voltage.	
8	12	12	PGND	G	Power ground pin, connected internally to the low side power FET. Connect to system ground, PAD, AGND, ground pins of C_{IN} and C_{OUT} . Path to C_{IN} must be as short as possible.	
9	13	13	PAD	G	Low impedance connection to AGND. Connect to PGND on PCB. Major heat dissipation path of the die. Must be used for heat sinking to ground plane on PCB.	
N/A	11	11	NC	N/A	Not for use. Leave this pin floating.	

(1) A = Analog, P = Power, G = Ground.



7 Specifications

7.1 Absolute Maximum Ratings

Over the recommended operating junction temperature range of -40° C to $+125^{\circ}$ C (unless otherwise noted)⁽¹⁾

PARAMETER		MIN	MAX	UNIT	
	VIN to PGND	-0.3	42		
	EN/SYNC to AGND	-5.5	V _{IN} + 0.3		
Input voltages	FB to AGND	-0.3	4.5	v	
Input voltages	RT to AGND	-0.3	4.5	v	
	PGOOD to AGND	-0.3	15		
	AGND to PGND	-0.3	0.3		
	SW to PGND	-1	V _{IN} + 0.3	- V	
Output valtages	SW to PGND less than 10 ns transients	-5	42		
Output voltages	BOOT to SW	-0.3	5.5		
	VCC to AGND	-0.3	4.5 ⁽²⁾		
TJ	J Junction temperature		150	°C	
T _{stg} Storage temperature		-65	150	°C	

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) In shutdown mode, the VCC to AGND maximum value is 5.25 V.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM) for HSOIC ⁽¹⁾		
		Human-body model (HBM) for WSON with RT and PGOOD ⁽¹⁾	±2500	v
		Charged-device model (CDM) for HSOIC and WSON RT ⁽²⁾	±1000	
		Charged-device model (CDM) for WSON PGOOD ⁽²⁾	±750	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

Over the recommended operating junction temperature range of -40°C to +125°C (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
	VIN	4	36	
Input voltage	EN/SYNC	-5	36	V
	FB	-0.3	1.2	v
	PGOOD	-0.3	12	
Input current	PGOOD pin current	0	1	mA
Output voltage	V _{OUT}	1	28	V
Output current	I _{OUT}	0	3	A
Temperature	Operating junction temperature, T_J	-40	125	°C

(1) Operating Ratings indicate conditions for which the device is intended to be functional, but do not ensure specific performance limits. For ensured specifications, see セクション 7.5.



7.4 Thermal Information

	THERMAL METRIC ⁽¹⁾ ⁽²⁾	DDA (8 PINS)	DRR (12 PINS)	UNIT
R _{θJA}	Junction-to-ambient thermal resistance	42.0	41.5	°C/W
ΨJT	Junction-to-top characterization parameter	5.9	0.3	°C/W
ΨЈВ	Junction-to-board characterization parameter	23.4	16.5	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	45.8	39.1	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	3.6	3.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	23.4	16.3	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

(2) Determine power rating at a specific ambient temperature T_A with a maximum junction temperature (T_J) of 125°C (see t/2s/7.3).

7.5 Electrical Characteristics

Limits apply over the recommended operating junction temperature (T_J) range of -40° C to $+125^{\circ}$ C, unless otherwise stated. Minimum and maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at T_J = 25 °C, and are provided for reference purposes only.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUF	PPLY (VIN PIN)	· · ·				
V _{IN}	Operation input voltage		4		36	V
VIN_UVLO	Undervoltage lockout thresholds	Rising threshold	3.3	3.7	3.9	V
		Falling threshold	2.9	3.3	3.5	v
I _{SHDN}	Shutdown supply current	$V_{EN} = 0 V, V_{IN} = 12 V, T_{J} = -40^{\circ}C \text{ to } 125^{\circ}C$		2	4	μA
l _Q	Operating quiescent current (non- switching)	V _{IN} =12 V, V _{FB} = 1.1 V, T _J = -40°C to 125°C, PFM mode		75		μA
ENABLE (EN	I/SYNC PIN)					
V _{EN_H}	Enable rising threshold voltage		1.4	1.55	1.7	V
V _{EN_HYS}	Enable hysteresis voltage			0.4		V
V _{WAKE}	Wake-up threshold		0.4			V
_		V_{IN} = 4 V to 36 V, V_{EN} = 2 V		10	100	nA nA
I _{EN}	Input leakage current at EN pin	V _{IN} = 4 V to 36 V, V _{EN} = 36 V			1	μA μA
VOLTAGE RI	EFERENCE (FB PIN)					h ., ,
\ <i>\</i>	Deference velkere	V_{IN} = 4.0 V to 36 V, T_J = 25 °C	0.985	1	1.015	V
V _{REF}	Reference voltage	V_{IN} = 4.0 V to 36 V, T _J = -40°C to 125°C	0.98	1	1.02	V
I _{LKG_FB}	Input leakage current at FB pin	V _{FB} = 1 V		10		nA

Limits apply over the recommended operating junction temperature (T_J) range of -40° C to $+125^{\circ}$ C, unless otherwise stated. Minimum and maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at T_J = 25 °C, and are provided for reference purposes only.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER GOO	DD (PGOOD PIN)		I			
V _{PG_OV}	Power-good flag overvoltage tripping threshold	% of reference voltage	104%	107%	110%	
V _{PG_UV}	Power-good flag undervoltage tripping threshold	% of reference voltage	92%	94%	96.5%	
V _{PG_HY} s	Power-good flag recovery hysteresis	% of reference voltage		1.5%		
V _{IN_PG_MIN}	Minimum V _{IN} for valid PGOOD output	50 μ A pullup to PGOOD pin, V _{EN} = 0 V, T _J = 25°C			1.5	V
		50 μ A pullup to PGOOD pin, V _{IN} = 1.5 V, V _{EN} = 0 V			0.4	V
V _{PG_LOW}	PGOOD low level output voltage	0.5 mA pullup to PGOOD pin, V _{IN} = 13.5 V, V _{EN} = 0 V			0.4	V
INTERNAL LI	DO (VCC PIN)	· · ·				
V _{CC}	Internal LDO output voltage			4.1		V
VCC UVLO	VCC undervoltage lockout	Rising threshold	2.8	3.2	3.6	V
	thresholds	Falling threshold	2.4	2.8	3.2	v
CURRENT LI	МІТ	· · ·				
l	S LIMIT Peak inductor current limit	HSOIC package	3.8	5	6.2	А
I _{HS_LIMIT}		WSON package	4	5.5	6.6	~
	Valley inductor current limit	HSOIC package	2.9	3.6	4.6	А
I _{LS_LIMIT}		WSON package	2.9	3.6	4.2	~
I _{L_ZC}	Zero cross current limit	HSOIC and WSON package		-0.04		А
I _{L_NEG}	Negative current limit (FPWM option)	SOIC and WSON package	-2.7	-2	-1.3	A
INTEGRATED	MOSFETS					
P	High-side MOSFET ON-resistance	SOIC package, V _{IN} = 12 V, I _{OUT} = 1 A		185		mΩ
R _{DS_ON_HS}		WSON package, V _{IN} = 12 V, I _{OUT} = 1 A		160		11152
R-a au ia	Low-side MOSFET ON-resistance	SOIC package, V _{IN} = 12 V, I _{OUT} = 1 A		105		mΩ
R _{DS_ON_LS}		WSON package, V _{IN} = 12 V, I _{OUT} = 1 A		95		11152
THERMAL SH	HUTDOWN					
T _{SHDN}	Thermal shutdown threshold		162	170	178	°C
T _{HYS}	Hysteresis			15		°C



7.6 Timing Requirements

Over the recommended operating junction temperature range of -40°C to +125°C (unless otherwise noted)

			MIN	NOM	MAX	UNIT
HICCUP MOI	DE		·			
N _{OC} ⁽¹⁾	Number of cycles that LS current limit is tripped to enter hiccup mode			64		Cycles
т	Hissup rathy dolay time	SOIC package		5		ms
T _{OC} Hiccup retry delay time		WSON package		10		1115
SOFT START	r					
T	lutere el e eft etert time e	SOIC package, the time of internal reference to increase from 0 V to 1 V		2		ms
T _{SS}	Internal soft-start time	WSON package, the time of internal reference to increase from 0 V to 1 V		6		ms
POWER GOO	סס	L				
T _{PGOOD_RISE}	Power-good flag rising transition deglitch delay			150		μs
T _{PGOOD_FALL}	Power-good flag falling transition deglitch delay			18		μs

(1) Ensured by design.

7.7 Switching Characteristics

Over the recommended operating junction temperature range of -40°C to +125°C (unless otherwise noted)

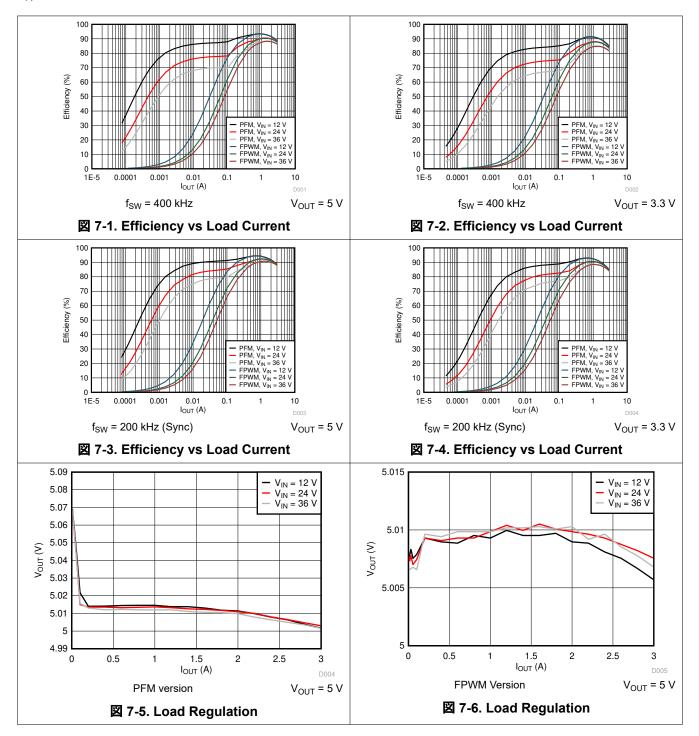
	PARAMETE	R	MIN	TYP	MAX	UNIT
SW (SW PIN)						
T _{ON_MIN}	Minimum turnon time	WSON package		60	90	ns
T _{OFF_MIN} ⁽¹⁾	Minimum turnoff time			100		ns
OSCILLATOR	(RT and EN/SYNC PIN)					
fsw_default	Oscillator default frequency	Fixed frequency version or RT pin open circuit	340	400	460	kHz
£	Minimum adjustable frequency	$R_T = 198 k\Omega$ with 1% accuracy	150	200	250	kHz
f _{ADJ}	Maximum adjustable frequency	$R_T = 17.8 \text{ k}\Omega$ with 1% accuracy	1750	2150	2425	kHz
f _{SYNC}	SYNC frequency range		200		2200	kHz
V _{SYNC}	Amplitude of SYNC clock AC signal (measured at SYNC pin)		2.8		5.5	V
T _{SYNC_MIN}	Minimum sync clock ON-time and OFF-time			100		ns

(1) Specified by design.

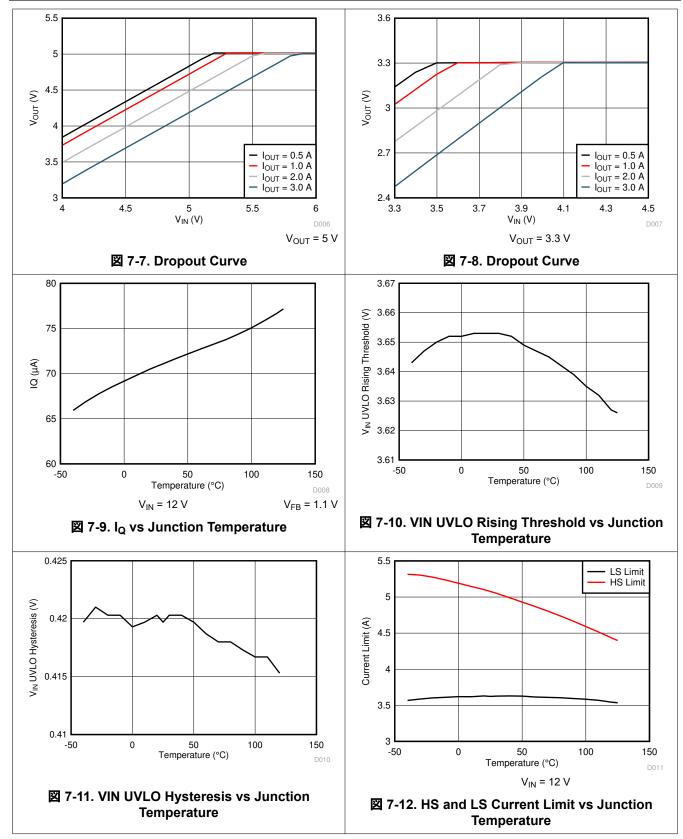


7.8 Typical Characteristics

Unless otherwise specified the following conditions apply: V_{IN} = 12 V, f_{SW} = 400 kHz, L = 8.2 µH, C_{OUT} = 150 µF, T_A = 25°C.









8 Detailed Description

8.1 Overview

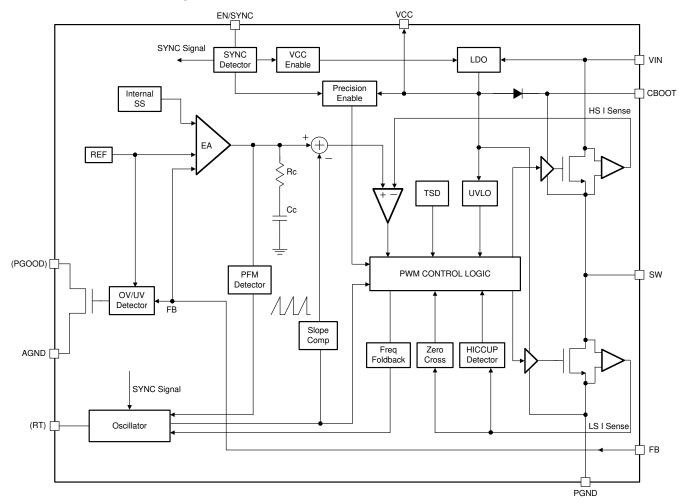
The LMR23630 SIMPLE SWITCHER[®] regulator is an easy-to-use synchronous step-down DC-DC converter operating from 4-V to 36-V supply voltage. The device delivers up to 3-A DC load current with good thermal performance in a small solution size. For both the HSOIC and WSON packages, an extended family is available in multiple current options from 1 A to 3 A in pin-to-pin compatible packages.

The LMR23630 employs constant frequency peak-current-mode control. The device enters PFM mode at light load to achieve high efficiency. A user-selectable FPWM version is provided to achieve low output voltage ripple, tight output voltage regulation, and constant switching frequency. The switching frequency is 400 kHz for the fixed-frequency version. For the version which has RT pin, the switching frequency is adjustable from 200 kHz to 2.2 MHz. The device is internally compensated, which reduces design time and requires few external components. The LMR23630 is capable of synchronization to an external clock within the range of 200 kHz to 2.2 MHz.

Additional features such as precision enable, power-good flag, and internal soft-start provide a flexible and easyto-use solution for a wide range of applications. Protection features include thermal shutdown, VIN and VCC undervoltage lockout, cycle-by-cycle current limit, and hiccup-mode short-circuit protection.

The family requires very few external components and has a pinout designed for simple, optimum PCB layout.

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 Fixed Frequency Peak Current Mode Control

The following operating description of the LMR23630 refers to tripies 8.2 and to the waveforms in 🛛 8-1. The LMR23630 is a step-down synchronous buck regulator with integrated high-side (HS) and low-side (LS) switches (synchronous rectifier). The LMR23630 supplies a regulated output voltage by turning on the HS and LS NMOS switches with controlled duty cycle. During high-side switch ON-time, the SW pin voltage swings up to approximately V_{IN} , and the inductor current i_L increase with linear slope ($V_{IN} - V_{OUT}$) / L. When the HS switch is turned off by the control logic, the LS switch is turned on after an anti-shoot-through dead time. Inductor current discharges through the LS switch with a slope of $-V_{OUT}$ / L. The control parameter of a buck converter is defined as duty cycle D = t_{ON} / T_{SW} , where t_{ON} is the high-side switch ON-time and T_{SW} is the switching period. The regulator control loop maintains a constant output voltage by adjusting the duty cycle D. In an ideal buck converter, where losses are ignored, D is proportional to the output voltage and inversely proportional to the input voltage: D = V_{OUT} / V_{IN} .

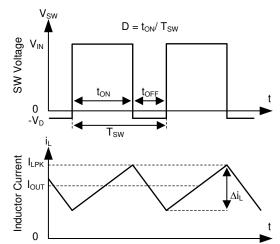


図 8-1. SW Node and Inductor Current Waveforms in Continuous Conduction Mode (CCM)

The LMR23630 employs fixed-frequency peak-current-mode control. A voltage feedback loop is used to get accurate DC voltage regulation by adjusting the peak current command based on voltage offset. The peak inductor current is sensed from the high-side switch and compared to the peak current threshold to control the ON-time of the high-side switch. The voltage feedback loop is internally compensated, which allows for fewer external components, makes it easy to design, and provides stable operation with almost any combination of output capacitors. The regulator operates with fixed switching frequency at normal load condition. At light load condition, the LMR23630 operates in PFM mode to maintain high efficiency (PFM option) or in FPWM mode for low output-voltage ripple, tight output-voltage regulation, and constant switching frequency (FPWM option).

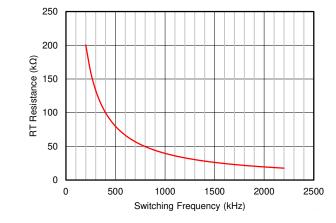
8.3.2 Adjustable Frequency

The switching frequency can be programmed for the adjustable-switching-frequency version of LMR23630 by the impedance R_T from the RT pin to ground. The frequency is inversely proportional to the R_T resistance. The RT pin can be left floating and the LMR23630 operates at 400-kHz default switching frequency. The RT pin is not designed to be shorted to ground. For a desired frequency, typical R_T resistance can be found by \vec{x} 1. 8-1gives typical R_T values for a given f_{SW}.

$$R_{T}(k\Omega) = 40200 / f_{SW}(kHz) - 0.6$$

(1)





1 8-2. RT vs Frequency Curve

f _{SW} (kHz)	$R_{\rm T}$ (kΩ)
200	200
350	115
500	78.7
750	53.6
1000	39.2
1500	26.1
2000	19.6
2200	17.8

表 8-1. Typical Frequency Setting RT Resistance

8.3.3 Adjustable Output Voltage

A precision 1-V reference voltage is used to maintain a tightly regulated output voltage over the entire operating temperature range. The output voltage is set by a resistor divider from output voltage to the FB pin. TI recommends using 1% tolerance resistors with a low temperature coefficient for the FB divider. Select the lowside resistor RFBB for the desired divider current and use Equation 2 to calculate high-side R_{FBT}. R_{FBT} in the range from 10 k Ω to 100 k Ω is recommended for most applications. A lower RFBT value can be used if static loading is desired to reduce VOUT offset in PFM operation. Lower RFBT will reduce efficiency at very light load. Less static current goes through a larger RFBT and might be more desirable when light load efficiency is critical. However, RFBT larger than 1 M Ω is not recommended because it makes the feedback path more susceptible to noise. Larger RFBT value requires more carefully designed feedback path on the PCB. The tolerance and temperature variation of the resistor dividers affect the output voltage regulation.

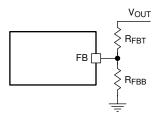


図 8-3. Output Voltage Setting

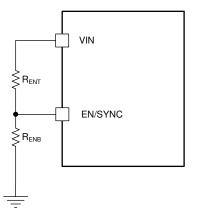
$$R_{FBT} = \frac{V_{OUT} - V_{REF}}{V_{REF}} \times R_{FBB}$$



8.3.4 Enable/Sync

The voltage on the EN/SYNC pin controls the ON or OFF operation of LMR23630. A voltage less than 1 V (typical) shuts down the device while a voltage higher than 1.6 V (typical) is required to start the regulator. The EN/SYNC pin is an input and cannot be left open or floating. The simplest way to enable the operation of the LMR23630 is to connect the EN to V_{IN} . This allows self-start-up of the LMR23630 when V_{IN} is within the operation range.

Many applications can benefit from the employment of an enable divider R_{ENT} and R_{ENB} (\boxtimes 8-4) to establish a precision system UVLO level for the converter. System UVLO can be used for supplies operating from utility power as well as battery power. It can be used for sequencing, ensuring reliable operation, or supply protection, such as a battery discharge level. An external logic signal can also be used to drive EN input for system sequencing and protection.





The EN pin also can be used to synchronize the internal oscillator to an external clock. The internal oscillator can be synchronized by AC-coupling a positive edge into the EN pin. The AC-coupled peak-to-peak voltage at the EN pin must exceed the SYNC amplitude threshold of 2.8 V (typical) to trip the internal synchronization pulse detector, and the minimum SYNC clock ON-time and OFF-time must be longer than 100 ns (typical). A 3.3-V or a higher amplitude pulse signal coupled through a 1-nF capacitor C_{SYNC} is a good starting point. Keeping R_{ENT} // R_{ENB} (R_{ENT} parallel with R_{ENB}) in the 100 k Ω range is a good choice. R_{ENT} is required for this synchronization circuit, but R_{ENB} can be left unmounted if system UVLO is not needed. LMR23630 switching action can be synchronized to an external clock from 200 kHz to 2.2 MHz. 🛛 8-6 and \bigotimes 8-7 show the device synchronized to an external system clock.

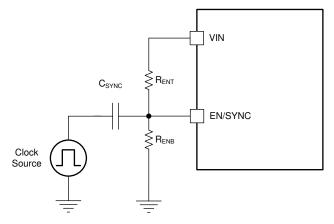
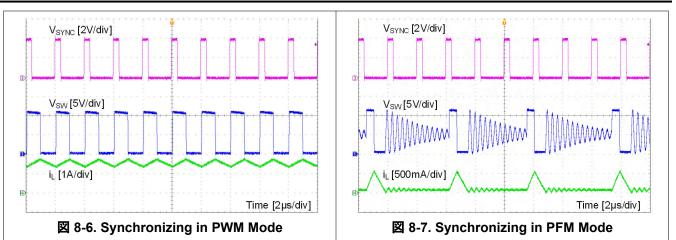


図 8-5. Synchronize to External Clock



8.3.5 VCC, UVLO

The LMR23630 integrates an internal LDO to generate V_{CC} for control circuitry and MOSFET drivers. The nominal voltage for V_{CC} is 4.1 V. The VCC pin is the output of an LDO and must be properly bypassed. Place a high-quality ceramic capacitor with a value of 2.2 μ F to 10 μ F, 16 V or higher rated voltage as close as possible to VCC and grounded to the exposed PAD and ground pins. The VCC output pin must not be loaded, or shorted to ground during operation. Shorting VCC to ground during operation may cause damage to the LMR23630.

VCC undervoltage lockout (UVLO) prevents the LMR23630 from operating until the V_{CC} voltage exceeds 3.3 V (typical). The VCC UVLO threshold has 400 mV (typical) of hysteresis to prevent undesired shutdown due to temporary V_{IN} drops.

8.3.6 Minimum ON-time, Minimum OFF-time and Frequency Foldback at Dropout Conditions

Minimum ON-time, T_{ON_MIN} , is the smallest duration of time that the HS switch can be on. T_{ON_MIN} is typically 60 ns in the LMR23630. Minimum OFF-time, T_{OFF_MIN} , is the smallest duration that the HS switch can be off. T_{OFF_MIN} is typically 100 ns in the LMR23630. In CCM operation, T_{ON_MIN} and T_{OFF_MIN} limit the voltage conversion range given a selected switching frequency.

The minimum duty cycle allowed is:

$$D_{MIN} = T_{ON MIN} \times f_{SW}$$
(3)

And the maximum duty cycle allowed is:

$$D_{MAX} = 1 - T_{OFF MIN} \times f_{SW}$$
(4)

Given fixed T_{ON_MIN} and T_{OFF_MIN} , the higher the switching frequency the narrower the range of the allowed duty cycle. In the LMR23630, a frequency foldback scheme is employed to extend the maximum duty cycle when T_{OFF_MIN} is reached. The switching frequency decreases once longer duty cycle is needed under low V_{IN} conditions. Wide range of frequency foldback allows the LMR23630 output voltage stay in regulation with a much lower supply voltage V_{IN} . This leads to a lower effective dropout voltage.

Given an output voltage, the choice of the switching frequency affects the allowed input voltage range, solution size and efficiency. The maximum operation supply voltage can be found by:

$$V_{IN_MAX} = \frac{V_{OUT}}{\left(f_{SW} \times T_{ON_MIN}\right)}$$
(5)

At lower supply voltage, the switching frequency decreases once T_{OFF_MIN} is tripped. The minimum V_{IN} without frequency foldback can be approximated by:

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(6)

$$V_{\text{IN}_{\text{MIN}}} = \frac{V_{\text{OUT}}}{\left(1 - f_{\text{SW}} \times T_{\text{OFF}_{\text{MIN}}}\right)}$$

Taking considerations of power losses in the system with heavy load operation, V_{IN_MAX} is higher than the result calculated in $\neq 5$. With frequency foldback, V_{IN_MIN} is lowered by decreased f_{SW} .

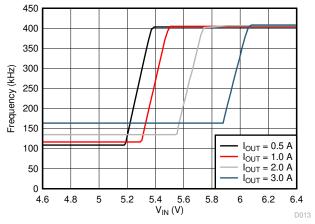
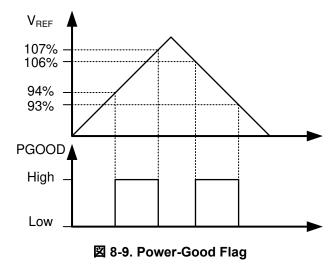


図 8-8. Frequency Foldback at Dropout (V_{OUT} = 5 V, f_{SW} = 400 kHz)

8.3.7 Power Good (PGOOD)

The power-good version of LMR23630 has a built in power-good flag shown on PGOOD pin to indicate whether the output voltage is within its regulation level. The PGOOD signal can be used for start-up sequencing of multiple rails or fault protection. The PGOOD pin is an open-drain output that requires a pullup resistor to an appropriate DC voltage. Voltage detected by the PGOOD pin must never exceed 15 V, and limit the maximum current into this pin to 1 mA. A typical range of pullup resistor value is 10 k Ω to 100 k Ω .

When the FB voltage is within the power-good band, +6% above and -6% below the internal reference voltage V_{REF} typically, the PGOOD switch is turned off, and the PGOOD voltage is as high as the pulled-up voltage. When the FB voltage is outside of the tolerance band, +7% above or -7% below V_{REF} typically, the PGOOD switch is turned on, and the PGOOD pin voltage is pulled low to indicate power bad. A glitch filter prevents false flag operation for short excursions in the output voltage, such as during line and load transients. The values for the various filter and delay times can be found in $\frac{1}{2}\sqrt{2}\sqrt{2}\sqrt{7.6}$. Power-good operation can best be understood by reference to $\boxed{8}$ 8-9.





8.3.8 Internal Compensation and C_{FF}

The LMR23630 is internally compensated as shown in 272328.2. The internal compensation is designed so that the loop response is stable over the entire operating frequency and output voltage range. Depending on the output voltage, the compensation loop phase margin can be low with all ceramic capacitors. TI recommends an external feed-forward capacitor C_{FF} be placed in parallel with the top resistor divider R_{FBT} for optimum transient performance.

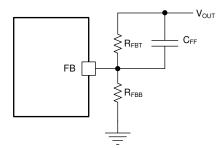


図 8-10. Feed-forward Capacitor for Loop Compensation

The feed-forward capacitor C_{FF} in parallel with R_{FBT} places an additional zero before the crossover frequency of the control loop to boost phase margin. The zero frequency can be found by:

$$f_{Z_{CFF}} = \frac{1}{\left(2\pi \times C_{FF} \times R_{FBT}\right)}$$
(7)

An additional pole is also introduced with C_{FF} at the frequency of:

$$f_{P_{CFF}} = \frac{1}{\left(2\pi \times C_{FF} \times R_{FBT} / / R_{FBB}\right)}$$
(8)

The zero f_{Z_CFF} adds phase boost at the crossover frequency and improves transient response. The pole f_{P-CFF} helps maintaining proper gain margin at frequency beyond the crossover. $\pm 9-1$ lists the combination of C_{OUT} , C_{FF} and R_{FBT} for typical applications, designs with similar C_{OUT} but R_{FBT} other than recommended value, adjust C_{FF} such that ($C_{FF} \times R_{FBT}$) is unchanged and adjust R_{FBB} such that (R_{FBT} / R_{FBB}) is unchanged.

Designs with different combinations of output capacitors need different C_{FF} . Different types of capacitors have different equivalent series resistance (ESR). Ceramic capacitors have the smallest ESR and need the most CFF. Electrolytic capacitors have much larger ESR than ceramic, and the ESR zero frequency location would be low enough to boost the phase up around the crossover frequency. Designs that use mostly electrolytic capacitors at the output may not need any CFF. The location of this ESR zero frequency can be calculated with Equation 9:

$$f_{Z_ESR} = \frac{1}{(2\pi \times C_{OUT} \times ESR)}$$
(9)

The C_{FF} creates a time constant with R_{FBT} that couples in the attenuate output voltage ripple to the FB node. If the C_{FF} value is too large, it can couple too much ripple to the FB and affect V_{OUT} regulation. Therefore, calculate C_{FF} based on output capacitors used in the system. At cold temperatures, the value of C_{FF} might change based on the tolerance of the chosen component. This may reduce its impedance and ease noise coupling on the FB node. To avoid this, more capacitance can be added to the output or the value of C_{FF} can be reduced.

8.3.9 Bootstrap Voltage (BOOT)

The LMR23630 provides an integrated bootstrap voltage regulator. A small capacitor between the BOOT and SW pins provides the gate drive voltage for the high-side MOSFET. The BOOT capacitor is refreshed when the high-side MOSFET is off and the low-side switch conducts. The recommended value of the BOOT capacitor is



0.1 µF to 0.47 µF. TI recommends a ceramic capacitor with an X7R or X5R grade dielectric with a voltage rating of 16 V or higherfor stable performance over temperature and voltage.

8.3.10 Overcurrent and Short-Circuit Protection

The LMR23630 is protected from over-current conditions by cycle-by-cycle current limit on both the peak and valley of the inductor current. Hiccup mode will be activated if a fault condition persists to prevent over-heating.

High-side MOSFET overcurrent protection is implemented by the nature of the peak-current-mode control. The HS switch current is sensed when the HS is turned on after a set blanking time. The HS switch current is compared to the output of the error amplifier (EA) minus slope compensation every switching cycle. See the $\frac{1}{2}$ $\frac{1}{2}$ 8.2 for more details. The peak current of HS switch is limited by a clamped maximum peak current threshold I_{HS_LIMIT} which is constant. Thus, the peak current limit of the high-side switch is not affected by the slope compensation and remains constant over the full duty cycle range.

The current going through LS MOSFET is also sensed and monitored. When the LS switch turns on, the inductor current begins to ramp down. The LS switch is not turned OFF at the end of a switching cycle if its current is above the LS current limit I_{LS_LIMIT} . The LS switch is kept ON so that inductor current keeps ramping down, until the inductor current ramps below the LS current limit I_{LS_LIMIT} . The LS switch is somewhat different than the more typical peak current limit and results in Equation 10 for the maximum load current.

$$I_{OUT_MAX} = I_{LS_LIMIT} + \frac{(V_{IN} - V_{OUT})}{2 \times f_{SW} \times L} \times \frac{V_{OUT}}{V_{IN}}$$
(10)

If the current of the LS switch is higher than the LS current limit for 64 consecutive cycles, hiccup current protection mode is activated. In hiccup mode, the regulator is shut down and kept off for 5 ms typically before the LMR23630 tries to start again. If overcurrent or short-circuit fault condition still exist, hiccup will repeat until the fault condition is removed. Hiccup mode reduces power dissipation under severe overcurrent conditions, prevents over-heating and potential damage to the device.

For FPWM version, the inductor current is allowed to go negative. If this current exceed I_{L_NEG} , the LS switch is turned off until the next clock cycle. This is used to protect the LS switch from excessive negative current.

8.3.11 Thermal Shutdown

The LMR23630 provides an internal thermal shutdown to protect the device when the junction temperature exceeds 170°C (typical). The device is turned off when thermal shutdown activates. Once the die temperature falls below 155°C (typical), the device reinitiates the power-up sequence controlled by the internal soft-start circuitry.



8.4 Device Functional Modes

8.4.1 Shutdown Mode

The EN pin provides electrical ON and OFF control for the LMR23630. When V_{EN} is below 1 V (typical), the device is in shutdown mode. The LMR23630 also employs VIN and VCC UVLO protection. If V_{IN} or V_{CC} voltage is below their respective UVLO level, the regulator is turned off.

8.4.2 Active Mode

The LMR23630 is in active mode when V_{EN} is above the precision enable threshold, V_{IN} and V_{CC} are above their respective UVLO level. The simplest way to enable the LMR23630 is to connect the EN pin to VIN pin. This allows self startup when the input voltage is in the operating range 4 V to 36 V. See $t/2y_{2} \times 8.3.5$ and $t/2y_{2} \times 8.3.4$ for details on setting these operating levels.

In active mode, depending on the load current, the LMR23630 is in one of four modes:

- 1. Continuous conduction mode (CCM) with fixed switching frequency when load current is above half of the peak-to-peak inductor current ripple (for both PFM and FPWM options).
- 2. Discontinuous conduction mode (DCM) with fixed switching frequency when load current is lower than half of the peak-to-peak inductor current ripple in CCM operation (only for PFM option).
- 3. Pulse frequency modulation mode (PFM) when switching frequency is decreased at very light load (only for PFM option).
- 4. Forced pulse width modulation mode (FPWM) with fixed switching frequency even at light load (only for FPWM option).

8.4.3 CCM Mode

CCM operation is employed in the LMR23630 when the load current is higher than half of the peak-to-peak inductor current. In CCM operation, the frequency of operation is fixed, output voltage ripple is at a minimum in this mode, and the maximum output current of 3 A can be supplied by the LMR23630.

8.4.4 Light Load Operation (PFM Version)

For PFM version, when the load current is lower than half of the peak-to-peak inductor current in CCM, the LMR23630 operates in DCM, also known as diode emulation mode (DEM). In DCM, the LS switch is turned off when the inductor current drops to $I_{L_{ZC}}$ (-40 mA typical). Both switching losses and conduction losses are reduced in DCM, compared to forced PWM operation at light load.

At even lighter current loads, PFM is activated to maintain high efficiency operation. When either the minimum HS switch ON-time (t_{ON_MIN}) or the minimum peak inductor current I_{PEAK_MIN} (300 mA typ) is reached, the switching frequency decreases to maintain regulation. In PFM, switching frequency is decreased by the control loop when load current reduces to maintain output voltage regulation. Switching loss is further reduced in PFM operation due to less frequent switching actions. The external clock synchronizing is not valid when the LMR23630 device enters into PFM mode.

8.4.5 Light Load Operation (FPWM Version)

For FPWM version, LMR23630 is locked in PWM mode at full load range. This operation is maintained, even at no-load, by allowing the inductor current to reverse its normal direction. This mode trades off reduced light load efficiency for low output voltage ripple, tight output voltage regulation, and constant switching frequency. In this mode, a negative current limit of I_{L_NEG} is imposed to prevent damage to the regulators low side FET. When in FPWM mode the converter synchronizes to any valid clock signal on the EN/SYNC input.



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LMR23630 is a step-down DC-to-DC regulator. It is typically used to convert a higher DC voltage to a lower DC voltage with a maximum output current of 3 A. The following design procedure can be used to select components for the LMR23630. Alternately, the WEBENCH[®] software may be used to generate complete designs. When generating a design, the WEBENCH[®] software utilizes iterative design procedure and accesses comprehensive databases of components. See www.ti.com for more details.

9.2 Typical Applications

The LMR23630 only requires a few external components to convert from a wide voltage-range supply to a fixed output voltage. \boxtimes 9-1 shows a basic schematic.

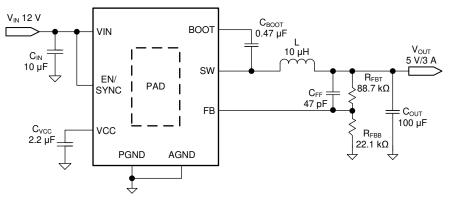


図 9-1. LM23630 Application Circuit

The external components must fulfill the needs of the application, but also the stability criteria of the device control loop. $\frac{1}{2}$ 9-1 can be used to simplify the output filter component selection.

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f _{SW} (kHz)	V _{OUT} (V)	L (μH) ⁽²⁾	C _{OUT} (μF) ⁽³⁾	C _{FF} (pF)	R _{FBT} (kΩ) ^{(4) (5)}
	3.3	15	300	150	51
200	5	18	200	100	88.7
200	12	33	100	See ⁽¹⁾	243
	24	33	47	See ⁽¹⁾	510
	3.3	6.8	150	75	51
400	5	10	100	47	88.7
400	12	15	68	See ⁽¹⁾	243
	24	15	47	See ⁽¹⁾	510
1000	3.3	3.3	68	39	51
1000	5	4.7	47	25	88.7
2200	3.3	2.2	47	33	51
2200	5	2.2	33	18	88.7

(1) High ESR C_{OUT} gives enough phase boost and C_{FF} not needed.



- (2) Inductance value is calculated based on V_{IN} = 36 V.
- (3) All the C_{OUT} values are after derating. Add more when using ceramic capacitors.
- (4) $R_{FBT} = 0 \Omega$ for $V_{OUT} = 1 V$. $R_{FBB} = 22.1 k\Omega$ for all other V_{OUT} setting.
- (5) For designs with R_{FBT} other than recommended value, please adjust C_{FF} such that (C_{FF} × R_{FBT}) is unchanged and adjust R_{FBB} such that (R_{FBT} / R_{FBB}) is unchanged.

9.2.1 Design Requirements

Detailed design procedure is described based on a design example. For this design example, use the parameters listed in $\frac{1}{5}$ 9-2 as the input parameters.

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage, V _{IN}	12 V typical, range from 8 V to 28 V
Output voltage, V _{OUT}	5 V
Maximum output current IO_MAX	3 A
Transient response 0.2 A to 2.5 A	5%
Output voltage ripple	50 mV
Input voltage ripple	400 mV
Switching frequency f _{SW}	400 kHz

表 9-2. Design Example Parameters

9.2.2 Detailed Design Procedure

9.2.2.1 Custom Design With WEBENCH® Tools

Click here to create a custom design using the LMR23625 device with the WEBENCH® Power Designer.

- 1. Start by entering the input voltage (V_{IN}), output voltage (V_{OUT}), and output current (I_{OUT}) requirements.
- 2. Optimize the design for key parameters such as efficiency, footprint, and cost using the optimizer dial.
- 3. Compare the generated design with other possible solutions from Texas Instruments.

The WEBENCH Power Designer provides a customized schematic along with a list of materials with real-time pricing and component availability.

In most cases, these actions are available:

- · Run electrical simulations to see important waveforms and circuit performance
- Run thermal simulations to understand board thermal performance
- · Export customized schematic and layout into popular CAD formats
- Print PDF reports for the design, and share the design with colleagues

Get more information about WEBENCH tools at www.ti.com/WEBENCH.

9.2.2.2 Output Voltage Setpoint

The output voltage of LMR23630 is externally adjustable using a resistor divider network. The divider network is comprised of top feedback resistor R_{FBT} and bottom feedback resistor R_{FBB} . Equation 11 is used to determine the output voltage:

$$R_{FBT} = \frac{V_{OUT} - V_{REF}}{V_{REF}} \times R_{FBB}$$
(11)

Choose the value of R_{FBB} to be 22.1 k Ω . With the desired output voltage set to 5 V and the V_{REF} = 1 V, the R_{FBB} value can then be calculated using Equation 11. The formula yields to a value 88.7 k Ω .

9.2.2.3 Switching Frequency

The default switching frequency of the LMR23630 is 400 kHz. For other switching frequency, the device must be synchronized to an external clock, see $\frac{1}{2}\sqrt{3} \times 8.3.4$ for more details.



9.2.2.4 Inductor Selection

The most critical parameters for the inductor are the inductance, saturation current, and the rated current. The inductance is based on the desired peak-to-peak ripple current Δi_L . Because the ripple current increases with the input voltage, the maximum input voltage is always used to calculate the minimum inductance L_{MIN} . Use Equation 12 to calculate the minimum value of the output inductor. K_{IND} is a coefficient that represents the amount of inductor ripple current relative to the maximum output current of the device. A reasonable value of K_{IND} should be 20% to 40%. During an instantaneous short or overcurrent operation event, the RMS and peak inductor current can be high. The inductor current rating should be higher than the current limit of the device.

$$\Delta i_{L} = \frac{V_{OUT} \times (V_{IN} MAX - V_{OUT})}{V_{IN} MAX \times L \times f_{SW}}$$
(12)

$$L_{MIN} = \frac{V_{IN}MAX - V_{OUT}}{I_{OUT} \times K_{IND}} \times \frac{V_{OUT}}{V_{IN}MAX \times f_{SW}}$$
(13)

In general, it is preferable to choose lower inductance in switching power supplies, because it usually corresponds to faster transient response, smaller DCR, and reduced size for more compact designs. However, inductance that is too low can generate an inductor current ripple that is too high so that overcurrent protection at the full load could be falsely triggered. It also generates more conduction loss and inductor core loss. Larger inductor current ripple also implies larger output voltage ripple with same output capacitors. With peak current mode control, TI does not recommend having an inductor current ripple that is too small. A larger peak-current ripple improves the comparator signal-to-noise ratio.

For this design example, choose $K_{IND} = 0.4$, the minimum inductor value is calculated to be 8.56 μ H. Choose the nearest standard 8.2 μ H ferrite inductor with a capability of 4-A RMS current and 6-A saturation current.

9.2.2.5 Output Capacitor Selection

Choose the output capacitor(s), C_{OUT}, with care because it directly affects the steady-state output-voltage ripple, loop stability, and the voltage over/undershoot during load-current transients.

The output ripple is essentially composed of two parts. One is caused by the inductor current ripple going through the equivalent series resistance (ESR) of the output capacitors:

$$\Delta V_{OUT_ESR} = \Delta i_{L} \times ESR = K_{IND} \times I_{OUT} \times ESR$$
⁽¹⁴⁾

The other is caused by the inductor current ripple charging and discharging the output capacitors:

$$\Delta V_{OUT_{C}} = \frac{\Delta i_{L}}{(8 \times f_{SW} \times C_{OUT})} = \frac{K_{IND} \times I_{OUT}}{(8 \times f_{SW} \times C_{OUT})}$$
(15)

The two components in the voltage ripple are not in phase, so the actual peak-to-peak ripple is smaller than the sum of two peaks.

Output capacitance is usually limited by transient performance specifications if the system requires tight voltage regulation with presence of large current steps and fast slew rate. When a fast large load increase happens, output capacitors provide the required charge before the inductor current can slew up to the appropriate level. The control loop of the regulator usually needs four or more clock cycles to respond to the output voltage droop. The output capacitance must be large enough to supply the current difference for four clock cycles to maintain the output voltage within the specified range. Equation 17 shows the minimum output capacitance needed for specified output undershoot. When a sudden large load decrease happens, the output capacitors absorb energy stored in the inductor. which results in an output voltage overshoot. Equation 14 calculates the minimum capacitance required to keep the voltage overshoot within a specified range.

(16)

(17)

$$C_{OUT} > \frac{4 \times (I_{OH} - I_{OL})}{f_{SW} \times V_{US}}$$

$$C_{OUT} > \frac{I_{OH}^2 - I_{OL}^2}{\left(V_{OUT} + V_{OS}\right)^2 - V_{OUT}^2} \times L$$

where

- I_{OL} = Low level output current during load transient
- I_{OH} = High level output current during load transient
- V_{US} = Target output voltage undershoot
- V_{OS} = Target output voltage overshoot

For this design example, the target output ripple is 50 mV. Presuppose $\Delta V_{OUT_ESR} = \Delta V_{OUT_C} = 50$ mV, and chose K_{IND} = 0.4. Equation 16 yields ESR no larger than 41.7 m Ω and Equation 17 yields C_{OUT} no smaller than 7.5 µF. For the target over/undershoot range of this design, $V_{US} = V_{OS} = 5\% \times V_{OUT} = 250$ mV. The C_{OUT} can be calculated to be no smaller than 108 µF and 28.5 µF by Equation 15 and Equation 17, respectively. Consider of derating, one 47-µF, 16-V and one 100-µF, 10-V ceramic capacitor with 5-m Ω ESR are used in parallel.

9.2.2.6 Feed-Forward Capacitor

The LMR23630 is internally compensated. Depending on the V_{OUT} and frequency f_{SW} , if the output capacitor C_{OUT} is dominated by low-ESR (ceramic types) capacitors, it could result in low phase margin. To improve the phase boost an external feed-forward capacitor C_{FF} can be added in parallel with R_{FBT}. C_{FF} is chosen such that phase margin is boosted at the crossover frequency without C_{FF}. A simple estimation for the crossover frequency (f_X) without C_{FF} is shown in Equation 18, assuming C_{OUT} has very small ESR, and C_{OUT} value is after derating.

$$f_{X} = \frac{8.32}{V_{OUT} \times C_{OUT}}$$
(18)

Equation 19 for C_{FF} was tested:

$$C_{FF} = \frac{1}{4\pi \times f_X \times R_{FBT}}$$
(19)

For designs with higher ESR, C_{FF} is not needed when C_{OUT} has very high ESR and C_{FF} calculated from Equation 19 must reduced with medium ESR. $\ge 9-1$ can be used as a quick starting point.

For the application in this design example, a 47-pF, 50-V, COG capacitor is selected.

9.2.2.7 Input Capacitor Selection

The LMR23630 device requires high-frequency input decoupling capacitor(s) and a bulk input capacitor, depending on the application. The typical recommended value for the high-frequency decoupling capacitor is 4.7 μ F to 10 μ F. TI recommends a high-quality ceramic capacitor type X5R or X7R with sufficiency voltage rating. To compensate the derating of ceramic capacitors, a voltage rating twice the maximum input voltage is recommended. Additionally, some bulk capacitance can be required, especially if the LMR23630 circuit is not located within approximately 5 cm from the input voltage source. This capacitor is used to provide damping to the voltage spike due to the lead inductance of the cable or the trace. For this design, two 4.7- μ F, 50-V, X7R ceramic capacitors are used. A 0.1- μ F for high-frequency filtering and place it as close as possible to the device pins.

9.2.2.8 Bootstrap Capacitor Selection

Every LMR23630 design requires a bootstrap capacitor (C_{BOOT}). TI recommends a capacitor of 0.47 μ F, ated 16 V or higher. The bootstrap capacitor is located between the SW pin and the BOOT pin. The bootstrap capacitor must be a high-quality ceramic type with an X7R or X5R grade dielectric for temperature stability.



9.2.2.9 VCC Capacitor Selection

The VCC pin is the output of an internal LDO for LMR23630. To insure stability of the device, place a minimum of 2.2-µF, 16V, X7R capacitor from this pin to ground.

9.2.2.10 Undervoltage Lockout Setpoint

The system undervoltage lockout (UVLO) is adjusted using the external voltage divider network of R_{ENT} and R_{ENB} . The UVLO has two thresholds, one for power up when the input voltage is rising and one for power down or brown outs when the input voltage is falling. The following equation can be used to determine the V_{IN} UVLO level.

$$V_{\text{IN}_{\text{RISING}}} = V_{\text{ENH}} \times \frac{R_{\text{ENT}} + R_{\text{ENB}}}{R_{\text{ENB}}}$$
(20)

The EN rising threshold (V_{ENH}) for LMR23630 is set to be 1.55 V (typical). Choose the value of R_{ENB} to be 287 k Ω to minimize input current from the supply. If the desired V_{IN} UVLO level is at 6 V, then the value of R_{ENT} can be calculated using Equation 21:

$$R_{ENT} = \left(\frac{V_{IN}RISING}{V_{ENH}} - 1\right) \times R_{ENB}$$
(21)

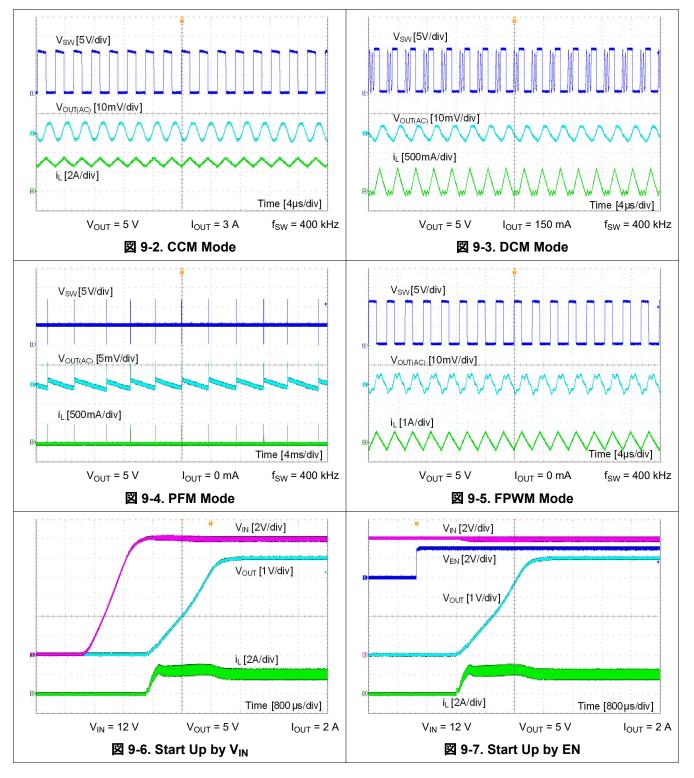
Equation 21 yields a value of 820 k Ω . The resulting falling UVLO threshold, equals 4.4 V, can be calculated by Equation 22, where EN hysteresis (V_{EN HYS}) is 0.4 V (typical).

$$V_{\text{IN}_{\text{FALLING}}} = \left(V_{\text{ENH}} - V_{\text{EN}_{\text{HYS}}}\right) \times \frac{R_{\text{ENT}} + R_{\text{ENB}}}{R_{\text{ENB}}}$$
(22)

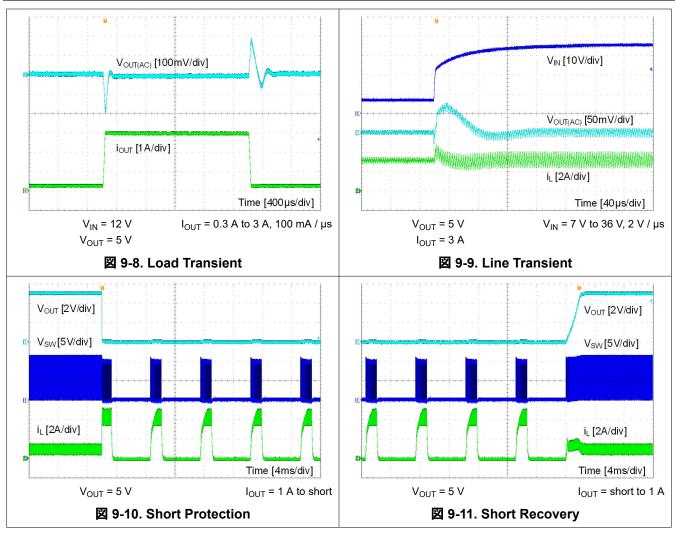


9.2.3 Application Curves

Unless otherwise specified the following conditions apply: V_{IN} = 12 V, f_{SW} = 400 kHz, L = 8.2 µH, C_{OUT} = 150 µF, T_A = 25 °C.









10 Power Supply Recommendations

The LMR23630 is designed to operate from an input voltage supply range between 4.5 V and 36 V for the HSOIC package and 4 V to 36 V for the WSON package. This input supply must be able to withstand the maximum input current and maintain a stable voltage. The resistance of the input supply rail must be low enough that an input current transient does not cause a high enough drop at the LMR23630 supply voltage that can cause a false UVLO fault triggering and system reset. If the input supply is located more than a few inches from the LMR23630, additional bulk capacitance may be required in addition to the ceramic input capacitors. The amount of bulk capacitance is not critical, but a 47-µF or 100-µF electrolytic capacitor is a typical choice.

11 Layout

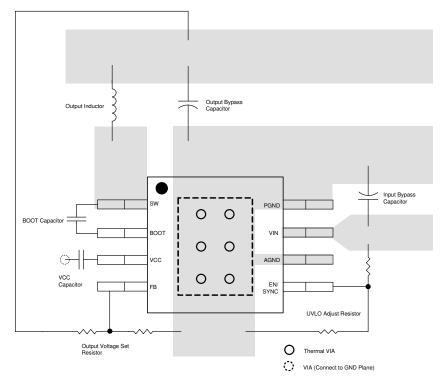
11.1 Layout Guidelines

Layout is a critical portion of good power supply design. The following guidelines will help users design a PCB with the best power conversion performance, thermal performance, and minimized generation of unwanted EMI.

- The input bypass capacitor C_{IN} must be placed as close as possible to the VIN and PGND pins. Grounding for both the input and output capacitors should consist of localized top side planes that connect to the PGND pin and PAD.
- 2. Place bypass capacitors for V_{CC} close to the VCC pin and ground the bypass capacitor to device ground.
- Minimize trace length to the FB pin net. Both feedback resistors, R_{FBT} and R_{FBB} should be located close to the FB pin. Place C_{FF} directly in parallel with R_{FBT}. If V_{OUT} accuracy at the load is important, make sure V_{OUT} sense is made at the load. Route V_{OUT} sense path away from noisy nodes and preferably through a layer on the other side of a shielded layer.
- 4. Use ground plane in one of the middle layers as noise shielding and heat dissipation path.
- 5. Have a single point ground connection to the plane. The ground connections for the feedback and enable components should be routed to the ground plane. This prevents any switched or load currents from flowing in the analog ground traces. If not properly handled, poor grounding can result in degraded load regulation or erratic output voltage ripple behavior.
- 6. Make V_{IN}, V_{OUT} and ground bus connections as wide as possible. This reduces any voltage drops on the input or output paths of the converter and maximizes efficiency.
- 7. Provide adequate device heat-sinking. Use an array of heat-sinking vias to connect the exposed pad to the ground plane on the bottom PCB layer. If the PCB has multiple copper layers, these thermal vias can also be connected to inner layer heat-spreading ground planes. Ensure enough copper area is used for heat-sinking to keep the junction temperature below 125 °C.



11.2 Layout Example





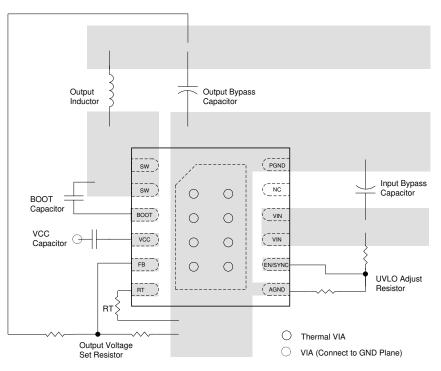


図 11-2. Sample WSON Package Layout

11.3 Compact Layout for EMI Reduction

Radiated EMI is generated by the high di/dt components in pulsing currents in switching converters. The larger area covered by the path of a pulsing current, the more EMI is generated. High frequency ceramic bypass



capacitors at the input side provide primary path for the high di/dt components of the pulsing current. Placing ceramic bypass capacitor(s) as close as possible to the VIN and PGND pins is the key to EMI reduction.

The SW pin connecting to the inductor must be as short as possible and just wide enough to carry the load current without excessive heating. Use short, thick traces or copper pours (shapes) high current conduction path to minimize parasitic resistance. Place the output capacitors close to the V_{OUT} end of the inductor and closely grounded to PGND pin and exposed PAD.

Place the bypass capacitors on VCC as close as possible to the pin and closely grounded to PGND and the exposed PAD.

11.4 Ground Plane and Thermal Considerations

TI recommends using one of the middle layers as a solid ground plane. Ground plane provides shielding for sensitive circuits and traces. It also provides a quiet reference potential for the control circuitry. Connect the AGND and PGND pins to the ground plane using vias right next to the bypass capacitors. PGND pin is connected to the source of the internal LS switch. They must be connected directly to the grounds of the input and output capacitors. The PGND net contains noise at switching frequency and may bounce due to load variations. PGND trace, as well as VIN and SW traces, must be constrained to one side of the ground plane. The other side of the ground plane contains much less noise and should be used for sensitive routes.

TI also recommends providing adequate device heat sinking by utilizing the PAD of the device as the primary thermal path. Use a minimum 4 by 2 array of 12 mil thermal vias to connect the PAD to the system ground plane heat sink. The vias should be evenly distributed under the PAD. Use as much copper as possible, for system ground plane, on the top and bottom layers for the best heat dissipation. Use a four-layer board with the copper thickness for the four layers, starting from the top of, 2 oz / 1 oz / 1 oz / 2 oz. Four-layer boards with enough copper thickness provides low current conduction impedance, proper shielding, and lower thermal resistance.

The thermal characteristics of the LMR23630 are specified using the parameter $R_{\theta JA}$, which characterize the junction temperature of silicon to the ambient temperature in a specific system. Although the value of $R_{\theta JA}$ is dependent on many variables, it still can be used to approximate the operating junction temperature of the device. To obtain an estimate of the device junction temperature, one may use the following relationship:

$$T_{\rm J} = P_{\rm D} \times R_{\rm \theta JA} + T_{\rm A} \tag{23}$$

$$P_{D} = V_{IN} \times I_{IN} \times (1 - \text{Efficiency}) - 1.1 \times I_{OUT}^{2} \times \text{DCR in watt}$$
(24)

where

- T_J = junction temperature in °C
- P_D = device power dissipation in watt
- $R_{\theta JA}$ = junction-to-ambient thermal resistance of the device in °C/W
- T_A = ambient temperature in °C
- DCR = inductor DC parasitic resistance in ohm

The maximum operating junction temperature of the LMR23630 is 125° C. R_{0JA} is highly related to PCB size and layout, as well as environmental factors such as heat sinking and air flow.



11.5 Feedback Resistors

To reduce noise sensitivity of the output voltage feedback path, it is important to place the resistor divider and C_{FF} close to the FB pin, rather than close to the load. The FB pin is the input to the error amplifier, so it is a high impedance node and very sensitive to noise. Placing the resistor divider and C_{FF} closer to the FB pin reduces the trace length of FB signal and reduces noise coupling. The output node is a low impedance node, so the trace from V_{OUT} to the resistor divider can be long if short path is not available.

If voltage accuracy at the load is important, make sure voltage sense is made at the load. Doing so corrects for voltage drops along the traces and provide the best output accuracy. The voltage sense trace from the load to the feedback resistor divider should be routed away from the SW node path and the inductor to avoid contaminating the feedback signal with switch noise, while also minimizing the trace length. This is most important when high value resistors are used to set the output voltage. TI recommends routing the voltage sense trace and place the resistor divider on a different layer than the inductor and SW node path, such that there is a ground plane in between the feedback trace and inductor/SW node polygon. This provides further shielding for the voltage feedback path from EMI noises.



12 Device and Documentation Support 12.1 Device Support

12.1.1 Development Support

12.1.1.1 Custom Design With WEBENCH® Tools

Click here to create a custom design using the LMR23625 device with the WEBENCH® Power Designer.

- 1. Start by entering the input voltage (V_{IN}), output voltage (V_{OUT}), and output current (I_{OUT}) requirements.
- 2. Optimize the design for key parameters such as efficiency, footprint, and cost using the optimizer dial.
- 3. Compare the generated design with other possible solutions from Texas Instruments.

The WEBENCH Power Designer provides a customized schematic along with a list of materials with real-time pricing and component availability.

In most cases, these actions are available:

- · Run electrical simulations to see important waveforms and circuit performance
- Run thermal simulations to understand board thermal performance
- Export customized schematic and layout into popular CAD formats
- Print PDF reports for the design, and share the design with colleagues

Get more information about WEBENCH tools at www.ti.com/WEBENCH.

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

PowerPAD[™] is a trademark of TI. TI E2E[™] is a trademark of Texas Instruments. SIMPLE SWITCHER[®] is a registered trademark of TI. WEBENCH[®] is a registered trademark of Texas Instruments. すべての商標は、それぞれの所有者に帰属します。

12.5 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。 正しい ESD 対策をとらないと、 デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずか に変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(-)		•		-	x=/	(6)	(-)		()	
LMR23630ADDA	ACTIVE	SO PowerPAD	DDA	8	75	RoHS & Green	NIPDAU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	F30A	Samples
LMR23630ADDAR	ACTIVE	SO PowerPAD	DDA	8	2500	RoHS & Green	NIPDAU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	F30A	Samples
LMR23630AFDDA	ACTIVE	SO PowerPAD	DDA	8	75	RoHS & Green	NIPDAU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	F30AF	Samples
LMR23630AFDDAR	ACTIVE	SO PowerPAD	DDA	8	2500	RoHS & Green	NIPDAU NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	F30AF	Samples
LMR23630APDRRR	ACTIVE	WSON	DRR	12	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	3630P	Samples
LMR23630APDRRT	ACTIVE	WSON	DRR	12	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	3630P	Samples
LMR23630DRRR	ACTIVE	WSON	DRR	12	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	23630	Samples
LMR23630DRRT	ACTIVE	WSON	DRR	12	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	23630	Samples
LMR23630FDRRR	ACTIVE	WSON	DRR	12	3000	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	3630F	Samples
LMR23630FDRRT	ACTIVE	WSON	DRR	12	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 125	3630F	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



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PACKAGE OPTION ADDENDUM

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF LMR23630 :

Automotive : LMR23630-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



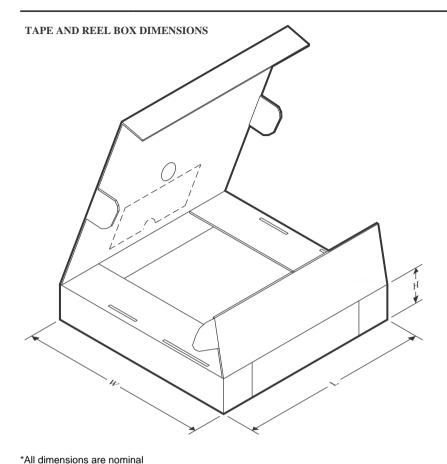
*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMR23630APDRRR	WSON	DRR	12	3000	330.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
LMR23630APDRRT	WSON	DRR	12	250	180.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
LMR23630DRRR	WSON	DRR	12	3000	330.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
LMR23630DRRT	WSON	DRR	12	250	180.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
LMR23630FDRRR	WSON	DRR	12	3000	330.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
LMR23630FDRRT	WSON	DRR	12	250	180.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2



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PACKAGE MATERIALS INFORMATION

4-Oct-2023



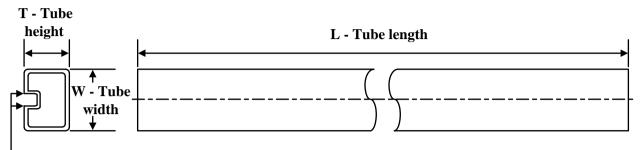
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)			
LMR23630APDRRR	WSON	DRR	12	3000	367.0	367.0	38.0			
LMR23630APDRRT	WSON	DRR	12	250	213.0	191.0	35.0			
LMR23630DRRR	WSON	DRR	12	3000	367.0	367.0	38.0			
LMR23630DRRT	WSON	DRR	12	250	213.0	191.0	35.0			
LMR23630FDRRR	WSON	DRR	12	3000	367.0	367.0	38.0			
LMR23630FDRRT	WSON	DRR	12	250	213.0	191.0	35.0			

TEXAS INSTRUMENTS

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4-Oct-2023

TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
LMR23630ADDA	DDA	HSOIC	8	75	517	7.87	635	4.25
LMR23630ADDA	DDA	HSOIC	8	75	507	8	3940	4.32
LMR23630AFDDA	DDA	HSOIC	8	75	507	8	3940	4.32
LMR23630AFDDA	DDA	HSOIC	8	75	517	7.87	635	4.25

DDA0008B



PACKAGE OUTLINE

PowerPAD[™] SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



NOTES:

PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MS-012.



DDA0008B

EXAMPLE BOARD LAYOUT

PowerPAD[™] SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002 (www.ti.com/lit/slma002) and SLMA004 (www.ti.com/lit/slma004).
- 9. Size of metal pad may vary due to creepage requirement.
- 10. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



DDA0008B

EXAMPLE STENCIL DESIGN

PowerPAD[™] SOIC - 1.7 mm max height

PLASTIC SMALL OUTLINE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



DDA (R-PDSO-G8)

PowerPAD ™ PLASTIC SMALL-OUTLINE



- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com http://www.ti.com.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. This package complies to JEDEC MS-012 variation BA

PowerPAD is a trademark of Texas Instruments.



DDA (R-PDSO-G8)

PowerPAD[™] PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD^{\mathbb{N}} package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

4206322-6/L 05/12

NOTE: A. All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments



DDA (R-PDSO-G8)

PowerPAD[™] PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads. PowerPAD is a trademark of Texas Instruments.



DRR 12

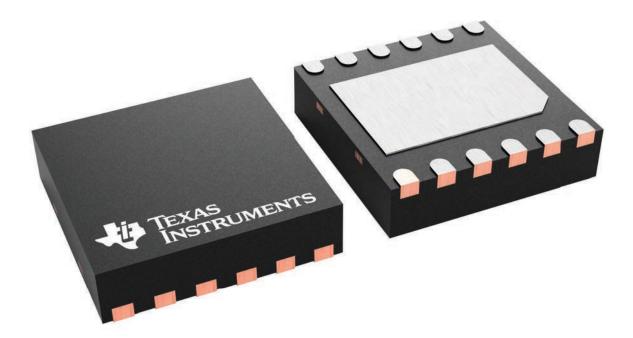
3 x 3, 0.5 mm pitch

GENERIC PACKAGE VIEW

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





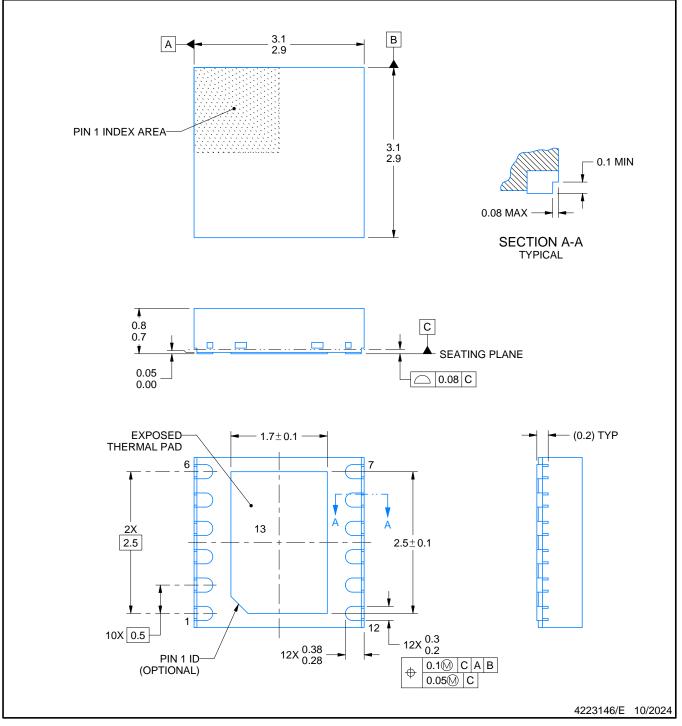
DRR0012D



PACKAGE OUTLINE

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.

3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

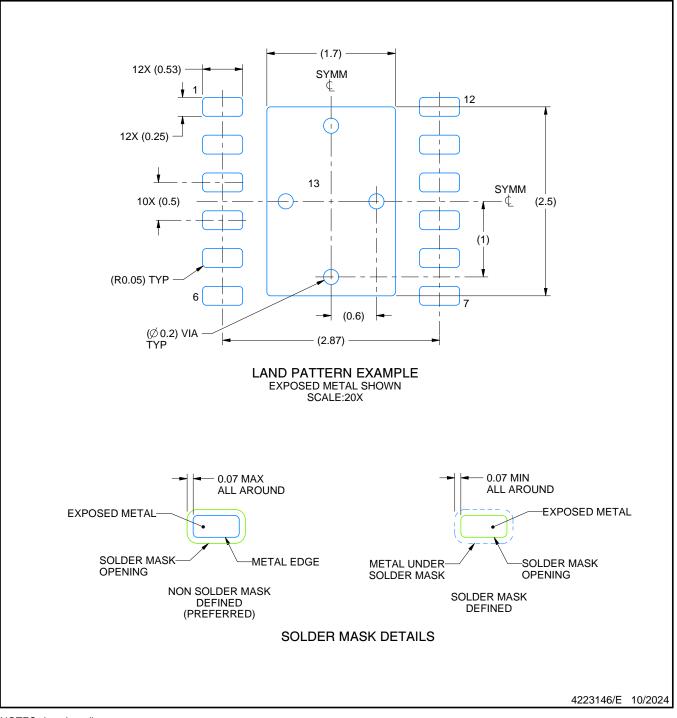


DRR0012D

EXAMPLE BOARD LAYOUT

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

 This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

 Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

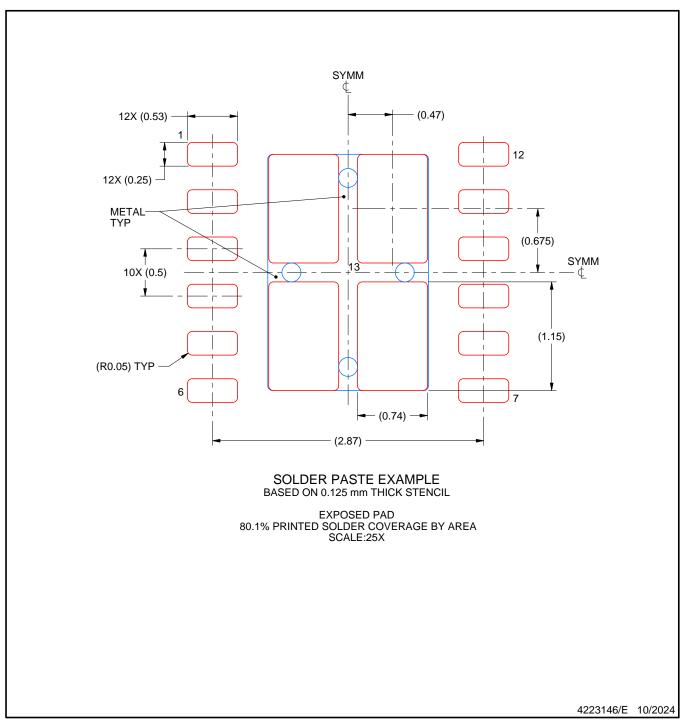


DRR0012D

EXAMPLE STENCIL DESIGN

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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